An ISO/TS16949 and ISO 9001 Certified Company

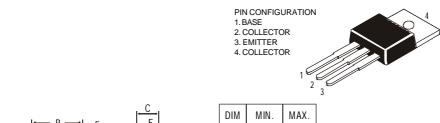


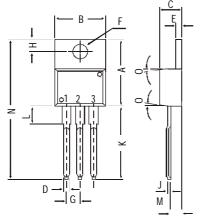
TO-220 Plastic Package

CSC2233

CSC2233 NPN PLASTIC POWER TRANSISTOR

TV Horizontal Deflection Output Applications





	DIM	MIN.	MAX.	
	Α	14.42	16.51	
diminsions in mm.	В	9.63	10.67	
	С	3.56	4.83	
	D		0.90	
	Ε	1.15	1.40	
	F	3.75	3.88	
	G	2.29	2.79	
	Н	2.54	3.43	
	J		0.56	
	K	12.70	14.73	
	L	2.80	4.07	
	М	2.03	2.92	
	N		31.24	
₹	0	DEG 7		

ABSOLUTE MAXIMUM RATINGS

Collector-base voltage (open emitter)	V_{CBO}	max.	200 V
Collector-emitter voltage (open base)	$V_{C\!E\!O}$	max.	60 V
Collector current	I_C	max.	4 A
Total power dissipation up to $T_C = 25^{\circ}C$	P_{tot}	max.	40 W
Junction temperature	T_j	max.	150 °C
Collector-emitter saturation voltage			
$I_C = 4 A; I_B = 0.4 A$	V_{CEsat}	max.	1.0 V
D.C. current gain			
$I_C = 1 A$; $V_{CE} = 5 V$	$h_{\!F\!E}$	min.	<i>30</i>
		max.	<i>150</i>

RATINGS (at T_A =25°C unless otherwise specified)

Limiting values

Collector-base voltage (open emitter)	V_{CBO}	max.	200 V
Collector-emitter voltage (open base)	$V_{C\!E\!O}$	max.	60 V
Emitter-base voltage (open collector)	V_{EBO}	max.	5.0 V
Collector current	I_C	max.	4 A
Collector current (Peak value)	I_{CP}	max.	10 A

CSC2233

Base current	I_B	max.	1.0 A
Total power dissipation up to $T_A = 25^{\circ}C$	\vec{P}_{tot}	max.	1.5 W
Total power dissipation up to $T_C = 25^{\circ}C$	P_{tot}	max.	40 W
Junction temperature		max.	150 ℃
Storage temperature	$T_{j} \ T_{stg}$	-65 to	+150 °C
	J		
CHARACTERISTICS			
$T_{amb} = 25$ °C unless otherwise specified			
Collector cutoff current			
$I_E = 0; \ V_{CB} = 170 \ V$	I_{CBO}	max.	$10 \mu A$
Emitter cut-off current			•
$I_C = 0$; $V_{EB} = 5 V$	I_{EBO}	max.	$10 \mu A$
Breakdown voltages			•
$I_C = 20 \text{ mA}; I_B = 0$	$V_{C\!E\!O}$	min.	60 V
$I_C = 1 \text{ mA}; I_E = 0$	V_{CBO}	min.	200 V
$I_E = 1 \text{ mA}; I_C = 0$	V_{EBO}	min.	5.0 V
Saturation voltages			
$I_C = 4 A$; $I_B = 0.4 A$	V_{CEsat}	max.	1.0 V
	V_{BEsat}	max.	1.5 V
D.C. current gain			
$I_C = 1 A; V_{CE} = 5 V$	$h_{\!F\!E}$	min.	<i>30</i>
		max.	<i>150</i>
IC = 4 A; $VCF = 5 V$	$h_{\!F\!E}$	min.	20
Transition frequency	111		
$I_C = 0.5 A; V_{CE} = 5 V$	f_T	typ.	8 MHz

Disclaimer

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